ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising an underlying film, a first electrode formed on the underlying film, a first dielectric film formed on the first electrode, a second electrode formed on the first dielectric film, and a first interconnect including a first conductive portion extending in a stack direction of the first electrode, the first dielectric film and the second electrode, a side surface of the first conductive portion being in contact with one of the first electrode and the second electrode.